

GM2907A

PNP EPITAXIAL PLANAR TRANSISTOR

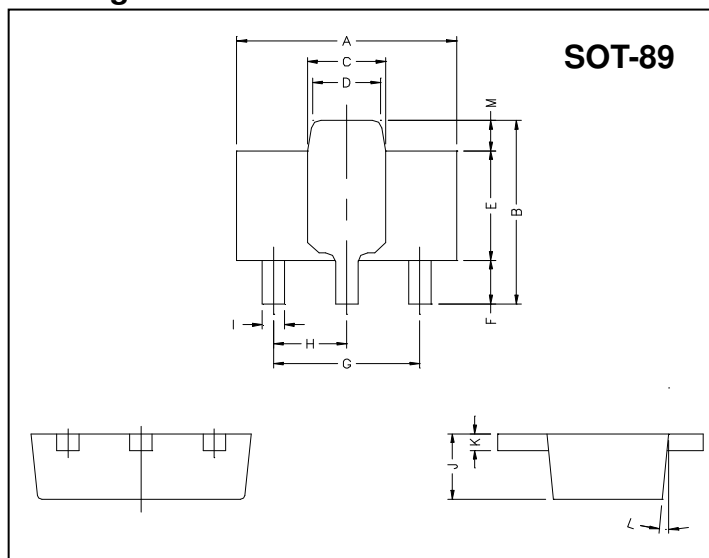
Description

The GM2907A is designed for general purpose amplifier and high speed switching, medium-power switching applications.

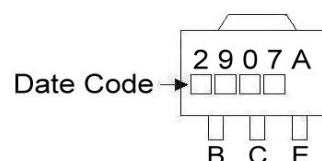
Features

- Low Collector Saturation Voltage
- High Speed Switching
- For Complementary Use With NPN Type GM2222A

Package Dimensions



Marking :



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.4	4.6	G	3.00	REF.
B	4.05	4.25	H	1.50	REF.
C	1.50	1.70	I	0.40	0.52
D	1.30	1.50	J	1.40	1.60
E	2.40	2.60	K	0.35	0.41
F	0.89	1.20	L	5°	TYP.
			M	0.70	REF.

Absolute Maximum Ratings at Ta = 25°C

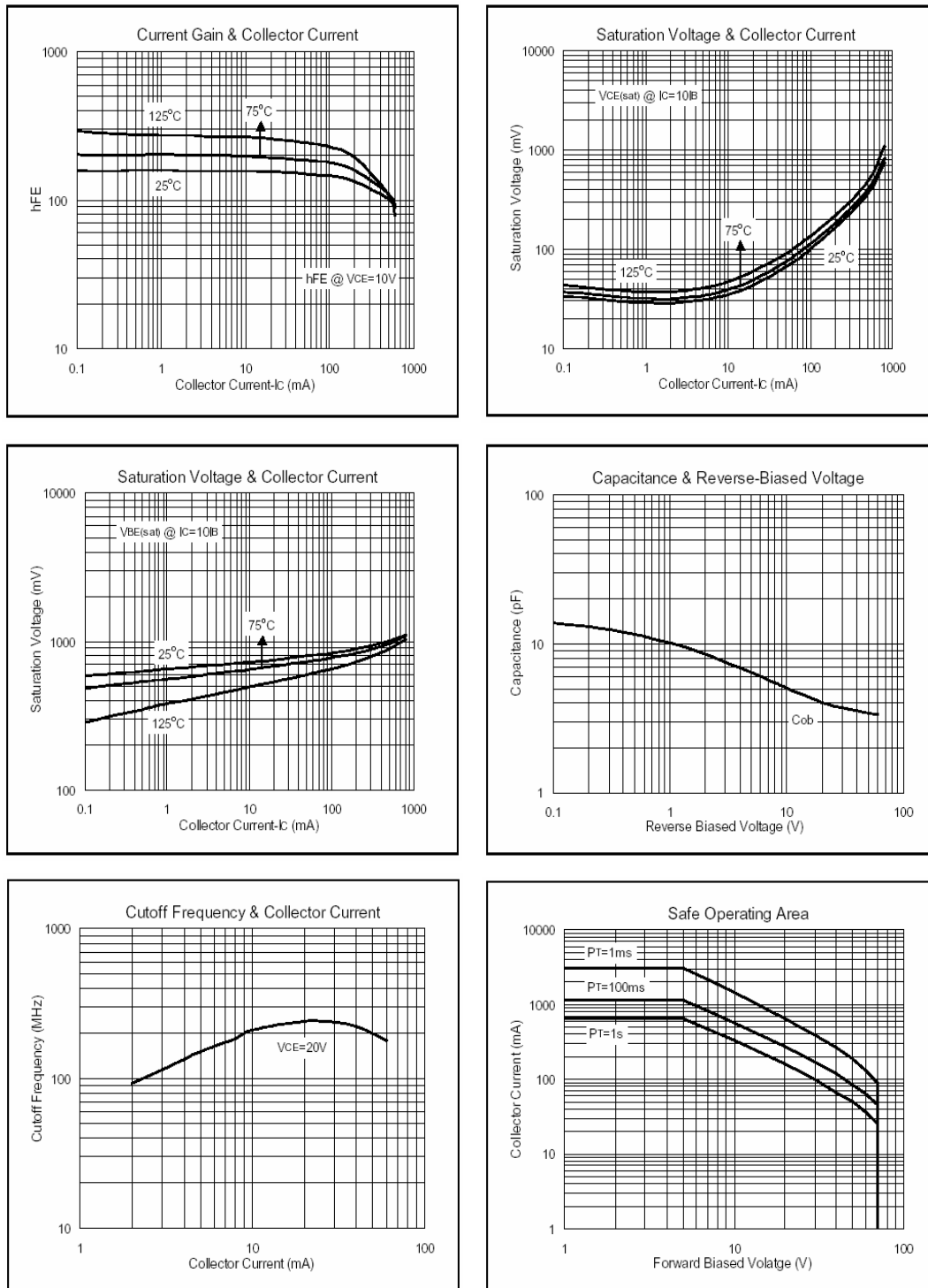
Parameter	Symbol	Ratings	Unit
Junction Temperature	T _j	+150	°C
Storage Temperature	T _{stg}	-55 ~ +150	°C
Collector to Base Voltage at Ta=25°C	V _{CB0}	-60	V
Collector to Emitter Voltage at Ta=25°C	V _{CE0}	-60	V
Emitter to Base Voltage at Ta=25°C	V _{EB0}	-5	V
Collector Current at Ta=25°C	I _C	-600	mA
Total Power Dissipation at Ta=25°C	P _D	1.2	W

Characteristics at Ta = 25°C

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
B _V CB0	-60	-	-	V	I _C =-10uA
B _V CE0	-60	-	-	V	I _C =-10mA
B _V EB0	-5	-	-	V	I _E =-10uA
I _C B0	-	-	-10	nA	V _{CE} =-50V
I _C EX	-	-	-50	nA	V _{CE} =-30V, V _{BE} =-0.5V
*V _{CE} (sat)1	-	-0.2	-0.4	V	I _C =-150mA, I _B =-15mA
*V _{CE} (sat)2	-	-0.5	-1.6	V	I _C =-500mA, I _B =-50mA
*V _{BE} (sat)1	-	-	-1.3	mV	I _C =-150mA, I _B =-15mA
*V _{BE} (sat)2	-	-	-2.6	V	I _C =-500mA, I _B =-50mA
*h _{FE} 1	75	-	-		V _{CE} =-10V, I _C =-0.1mA
*h _{FE} 2	100	-	-		V _{CE} =-10V, I _C =-1mA
*h _{FE} 3	100	-	-		V _{CE} =-10V, I _C =-10mA
*h _{FE} 4	100	-	300		V _{CE} =-10V, I _C =-150mA
*h _{FE} 5	50	-	-		V _{CE} =-10V, I _C =-500mA
f _T	200	-	-	MHz	V _{CE} =-20V, I _C =-50mA, f=100MHz
Cob	-	-	8.0	pF	V _{CE} =-10V, f=1MHz

* Pulse Test: Pulse Width ≤ 380μs, Duty Cycle ≤ 2%

Characteristics Curve



Important Notice:

- All rights are reserved. Reproduction in whole or in part is prohibited without the prior written approval of GTM.
- GTM reserves the right to make changes to its products without notice.
- GTM semiconductor products are not warranted to be suitable for use in life-support Applications, or systems.
- GTM assumes no liability for any consequence of customer product design, infringement of patents, or application assistance.

Head Office And Factory:

- **Taiwan:** No. 17-1 Tatung Rd. Fu Kou Hsin-Chu Industrial Park, Hsin-Chu, Taiwan, R. O. C.
TEL : 886-3-597-7061 FAX : 886-3-597-9220, 597-0785
- **China:** (201203) No.255, Jang-Jiang Tsai-Lueng RD. , Pu-Dung-Hsin District, Shang-Hai City, China
TEL : 86-21-5895-7671 ~ 4 FAX : 86-21-38950165